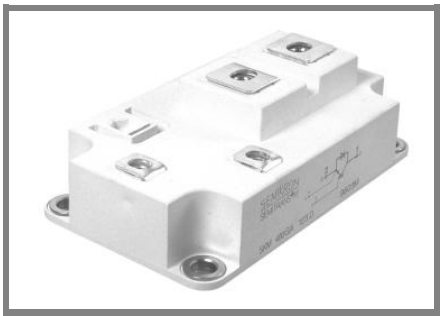
SKM 600GA125D



SEMITRANS® 4

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SKM 600GA125D

Features

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- Short circuit self limiting to 6 x I_c
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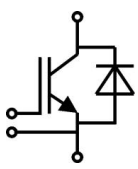

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Absolute Maximum Ratings			T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_{case} = 25 °C	580	A
		T_{case} = 80 °C	400	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		800	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	500	A
		T_{case} = 80 °C	350	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		800	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	3600	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40 ... + 150 (125)	°C
T_{stg}			125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics			T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 16 mA		4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,15	0,45	mA
V_{CE0}		T_j = 25 °C		1,5	1,75	V
		T_j = 125 °C		1,7		V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		4,5	5,3	mΩ
		T_j = 125°C		6		mΩ
$V_{CE(sat)}$	I_{Cnom} = 400 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		3,3	3,85	V
		T_j = 125°C$_{chiplev.}$		4		V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		36		nF
C_{oes}				3,8		nF
C_{res}				3,5		nF
Q_G	V_{GE} = -8V - +20V			4400		nC
R_{Gint}	T_j = °C			1,25		Ω
$t_{d(on)}$	R_{Gon} = 2,5 Ω	V_{CC} = 600V		80		ns
t_r		I_C= 400A		70		ns
E_{on}		T_j = 125 °C		30		mJ
$t_{d(off)}$	R_{Goff} = 2,5 Ω	V_{GE} = ± 15V		570		ns
t_f				60		ns
E_{off}						mJ
$R_{th(j-c)}$	per IGBT				0,041	K/W

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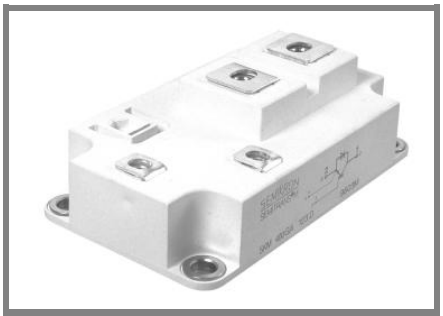
SKM 600GA125D



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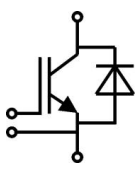

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Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 400 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2	2,5	V
		T_j = 125 °$C_{chiplev.}$		1,8		V
V_{F0}		T_j = 25 °C		1,1	1,2	V
		T_j = 125 °C				V
r_F		T_j = 25 °C		2,3	3,3	mΩ
		T_j = 125 °C				mΩ
I_{RRM}	I_F = 400 A	T_j = 125 °C		460		A
Q_{rr}				65		µC
E_{rr}	V_{GE} = 0 V; V_{CC} = 600 V					mJ
$R_{th(j-c)D}$	per diode				0,09	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= °C		0,18		mΩ
$R_{th(c-s)}$	per module				0,038	K/W
M_s	to heat sink		3		5	Nm
M_t	to terminals		2,5 (1,1)		5 (2)	Nm
w					330	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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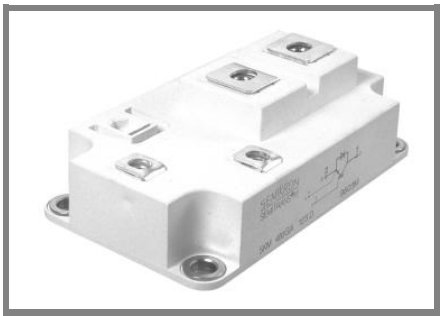

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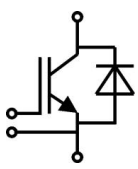

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Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	29	mk/W
R_i	i = 2	9	mk/W
R_i	i = 3	2,6	mk/W
R_i	i = 4	0,4	mk/W
tau_i	i = 1	0,1043	s
tau_i	i = 2	0,009	s
tau_i	i = 3	0,001	s
tau_i	i = 4	0,0002	s
$Z_{th(j-c)D}$			
R_i	i = 1	62	mk/W
R_i	i = 2	23	mk/W
R_i	i = 3	4,2	mk/W
R_i	i = 4	0,8	mk/W
tau_i	i = 1	0,0566	s
tau_i	i = 2	0,0166	s
tau_i	i = 3	0,0015	s
tau_i	i = 4	0,0002	s

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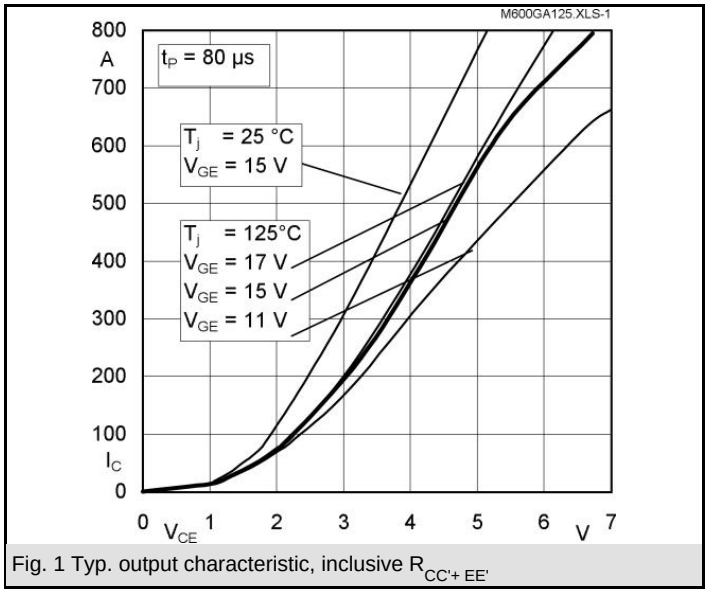

Fig. 1 Typ. output characteristic, inclusive $R_{CC'+ EE'}$

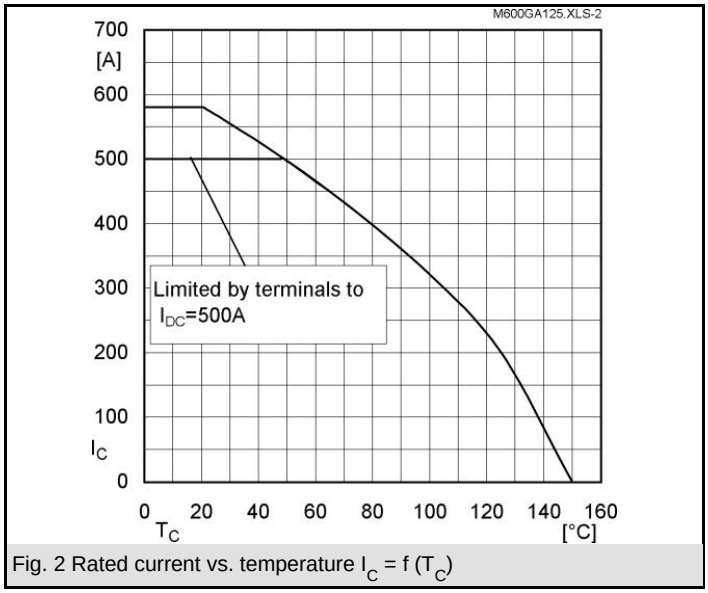

Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

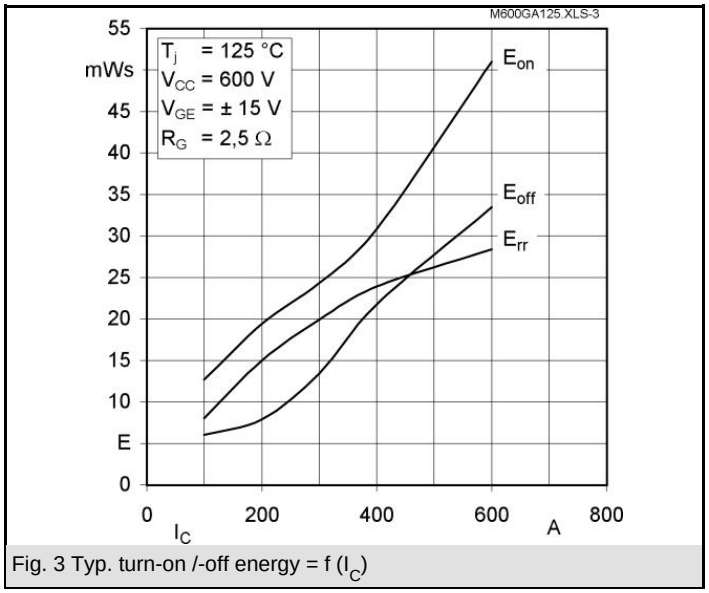

Fig. 3 Typ. turn-on /-off energy = f (I_C)

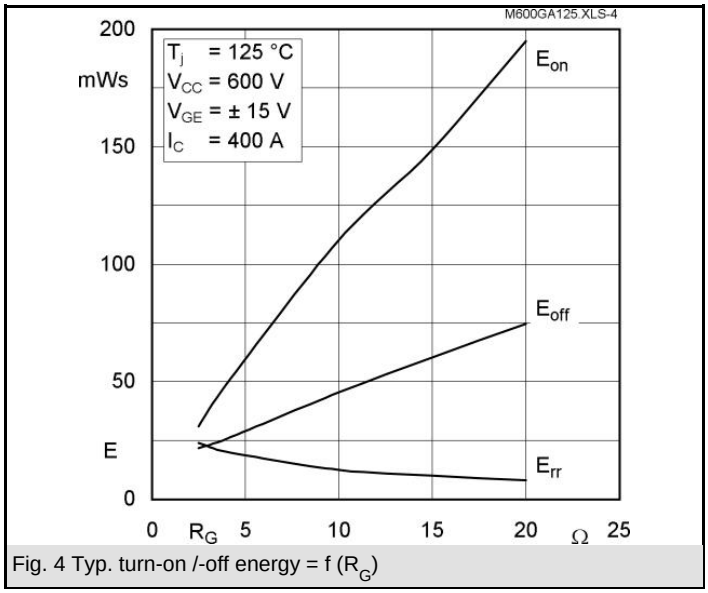

Fig. 4 Typ. turn-on /-off energy = f (R_G)

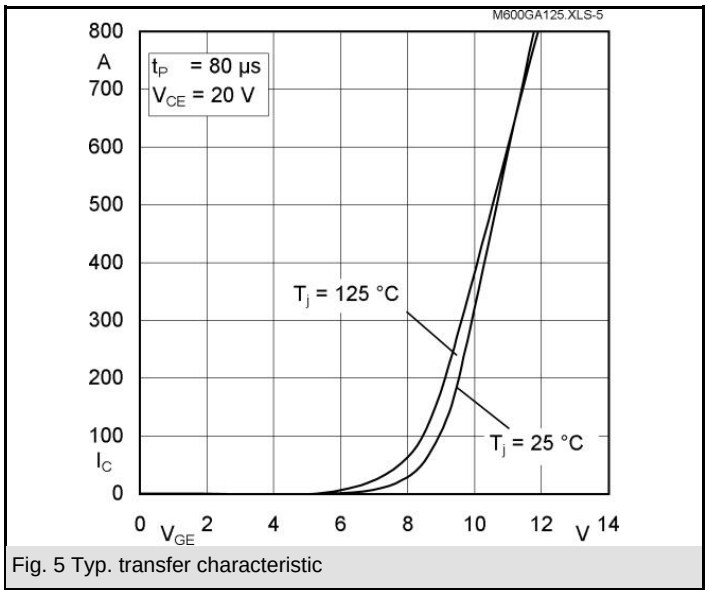

Fig. 5 Typ. transfer characteristic

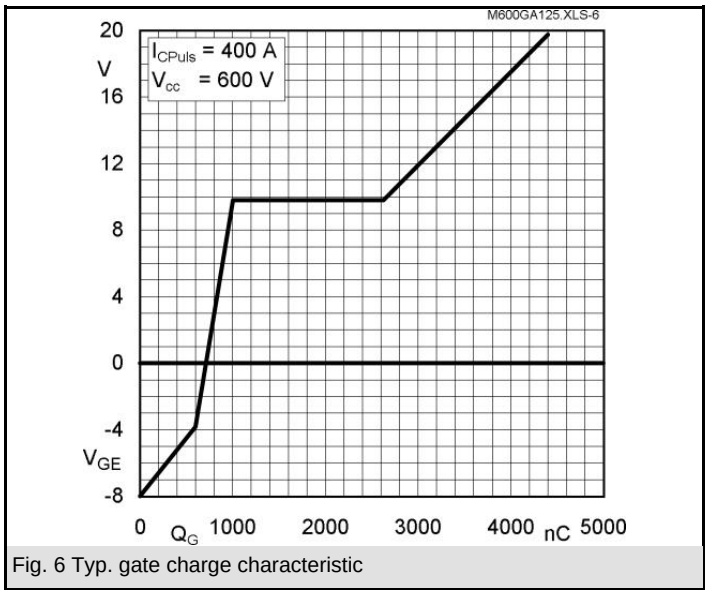

Fig. 6 Typ. gate charge characteristic

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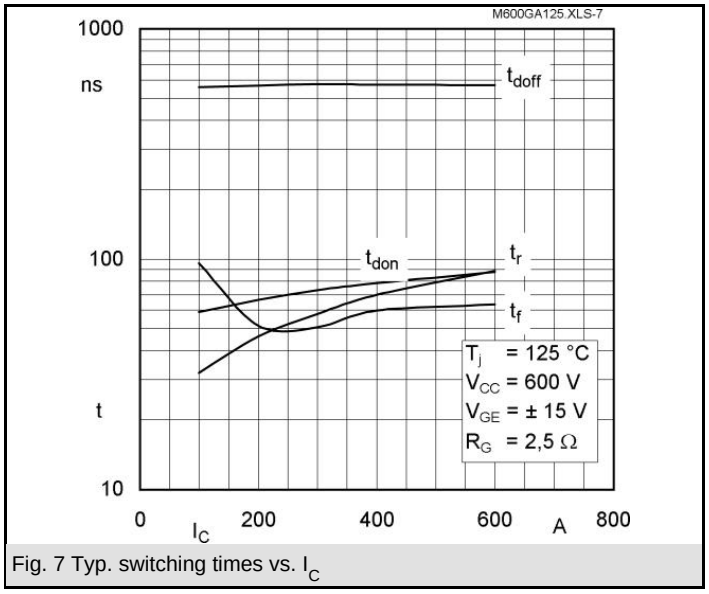

Fig. 7 Typ. switching times vs. I_C

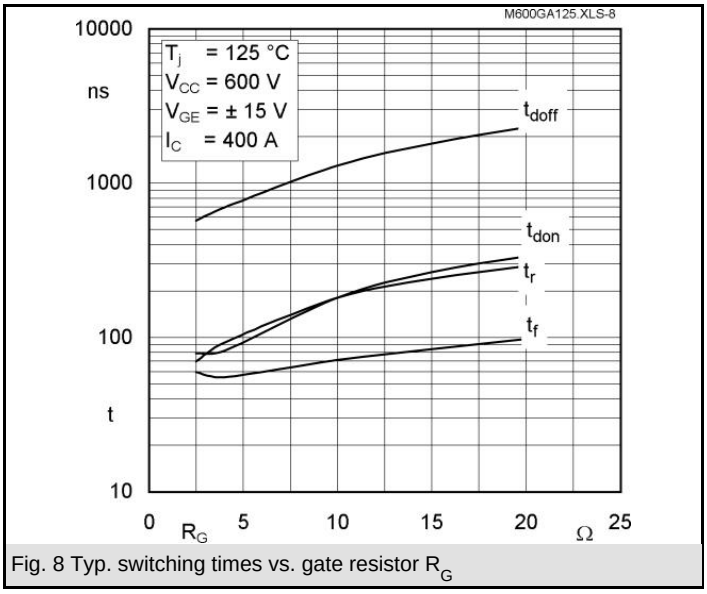

Fig. 8 Typ. switching times vs. gate resistor R_G

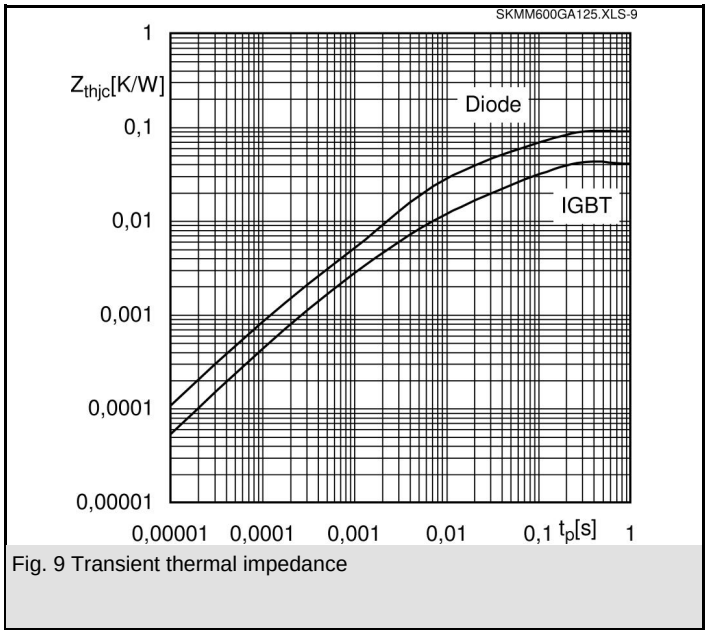

Fig. 9 Transient thermal impedance

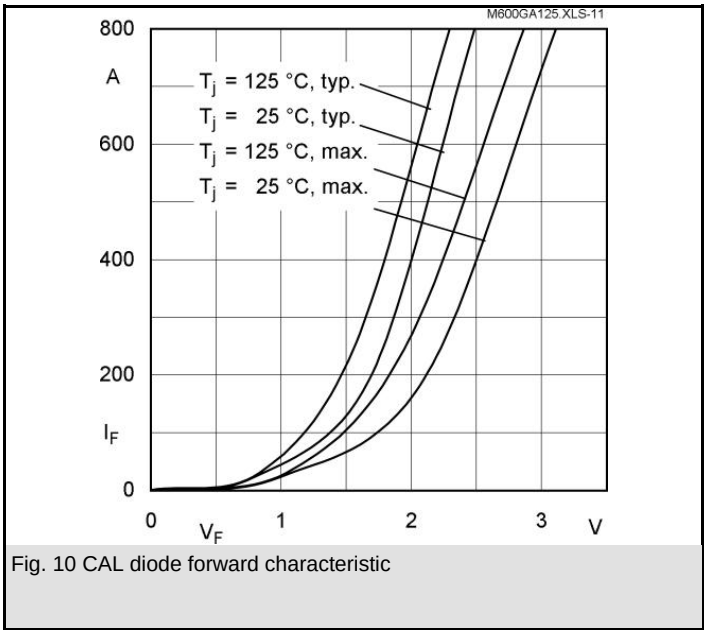

Fig. 10 CAL diode forward characteristic

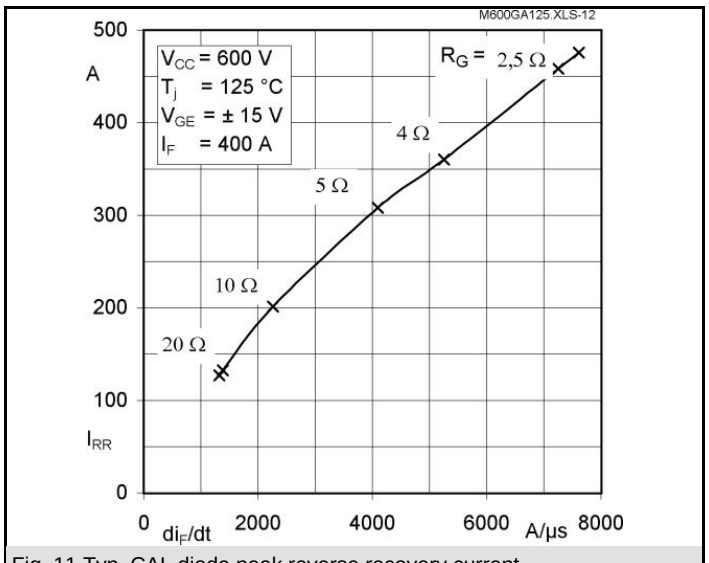

Fig. 11 Typ. CAL diode peak reverse recovery current

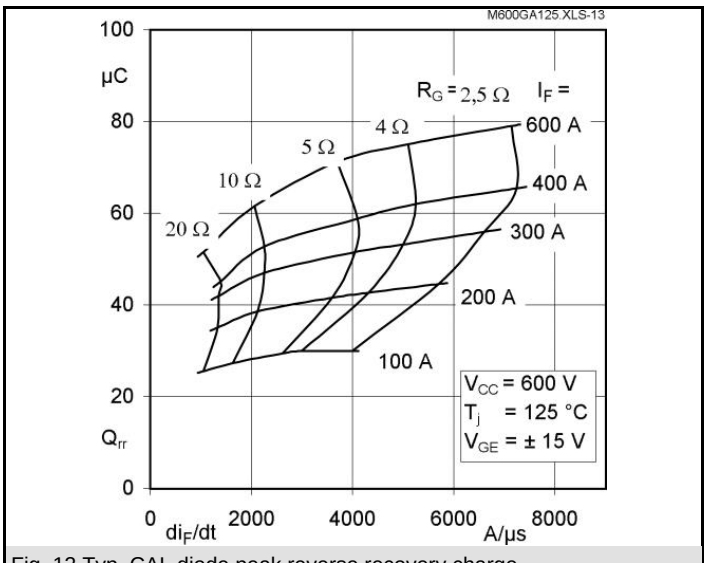

Fig. 12 Typ. CAL diode peak reverse recovery charge

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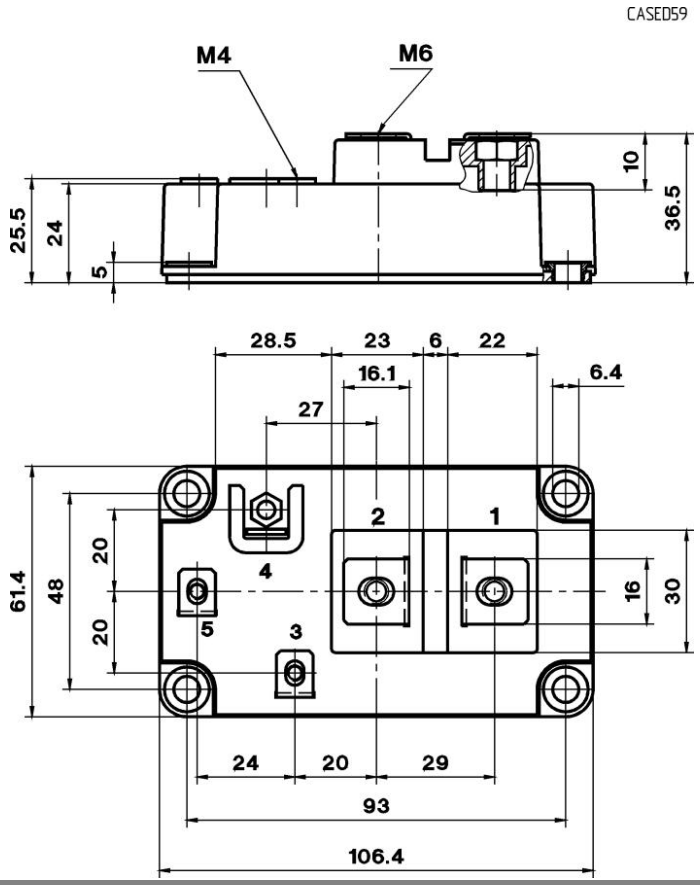
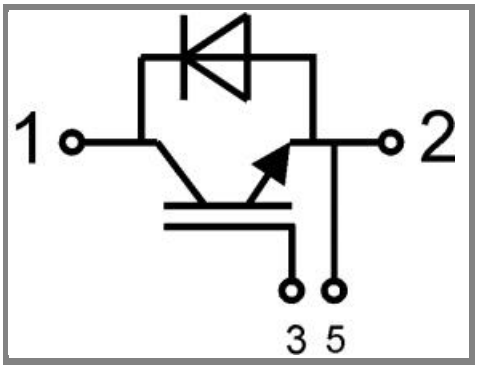


Case D 59



Case D59 GA

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